

NISTTech

Power Sensor

Description

This is a divisional U.S. patent. See U.S. parent patent under Citations below.

Abstract

A method for forming a single cavity in a substrate, which may extend approximately the length of a device located on top of the substrate, and device produced thereby. The device has a length and a width, and may extend approximately the length of the substrate. After locating the device on the surface of the substrate, a first etchant is applied through openings on the surface of the substrate. Subsequently, a second etchant is applied through the same openings on the surface of the substrate. As a result, a single cavity is formed beneath the surface of the device, suspending the device and minimizing electrical coupling.

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Citations

1. U.S. Parent Patent # 6,107,210

References

- Expired U.S. Patent #6,303,976 issued 10-16-2001
- Docket: 96-049D

Status of Availability

This technology is available in the public domain.

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